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(54) Title: DIRECT AND SELECTIVE MASS TRANSFER PROCESS FOR MICROLED DISPLAY FABRICATION

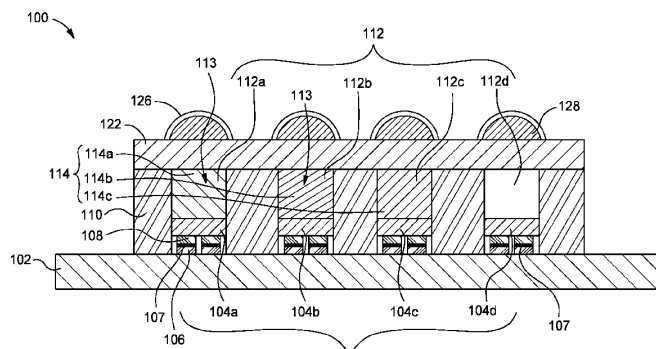


FIG. 1

(57) Abstract: Described herein are devices and methods for creating devices including a backplane, the backplane includes a plurality of backplane electrodes where each backplane electrode includes a first material. A plurality of micro-LEDs having a plurality of micro-LED electrodes, each micro-LED electrode including a second material, where each micro-LED electrode is bonded to each backplane electrode with an alloy of the first material and the second material therebetween. The device further includes a plurality of subpixel isolation (SI) structures formed over the backplane, the SI structures defining wells of subpixels, each well including a respective micro-LED between adjacent SI structures, and the subpixels having a color conversion material disposed in the wells.

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